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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	516096
Number of I/O	620
Number of Gates	3000000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-55°C ~ 125°C (TJ)
Package / Case	896-BGA
Supplier Device Package	896-FBGA (31x31)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3pe3000l-fgg896m

Reduced Cost of Ownership

Advantages to the designer extend beyond low unit cost, performance, and ease of use. Unlike SRAM-based FPGAs, flash-based military ProASIC3/EL devices allow all functionality to be live at power-up; no external boot PROM is required. On-board security mechanisms prevent access to all the programming information and enable secure remote updates of the FPGA logic. Designers can perform secure remote in-system reprogramming to support future design iterations and field upgrades with confidence that valuable intellectual property cannot be compromised or copied. Secure ISP can be performed using the industry-standard AES algorithm. The military ProASIC3/EL family device architecture mitigates the need for ASIC migration at higher volumes. This makes the military ProASIC3/EL family a cost-effective ASIC replacement.

Firm-Error Immunity

Firm errors occur most commonly when high-energy neutrons, generated in the upper atmosphere, strike a configuration cell of an SRAM FPGA. The energy of the collision can change the state of the configuration cell and thus change the logic, routing, or I/O behavior in an unpredictable way. These errors are impossible to prevent in SRAM FPGAs. The consequence of this type of error can be a complete system failure. Firm errors do not exist in the configuration memory of military ProASIC3/EL flash-based FPGAs. Once it is programmed, the flash cell configuration element of military ProASIC3/EL FPGAs cannot be altered by high-energy neutrons and is therefore immune to them. Recoverable (or soft) errors occur in the user data SRAM of all FPGA devices. These can easily be mitigated by using error detection and correction (EDAC) circuitry built into the FPGA fabric.

Advanced Flash Technology

The military ProASIC3/EL family offers many benefits, including nonvolatility and reprogrammability, through an advanced flash-based, 130-nm LVCMOS process with 7 layers of metal. Standard CMOS design techniques are used to implement logic and control functions. The combination of fine granularity, enhanced flexible routing resources, and abundant flash switches allows for very high logic utilization without compromising device routability or performance. Logic functions within the device are interconnected through a four-level routing hierarchy.

Advanced Architecture

The proprietary military ProASIC3/EL architecture provides granularity comparable to standard-cell ASICs. The military ProASIC3/EL device consists of five distinct and programmable architectural features ([Figure 1-1 on page 1-4](#) and [Figure 1-2 on page 1-4](#)):

- FPGA VersaTiles
- Dedicated FlashROM
- Dedicated SRAM/FIFO memory
- Extensive CCCs and PLLs
- I/O structure

The FPGA core consists of a sea of VersaTiles. Each VersaTile can be configured as a three-input logic function, a D-flip-flop (with or without enable), or a latch by programming the appropriate flash switch interconnections. The versatility of the military ProASIC3/EL core tile, as either a three-input lookup table (LUT) equivalent or a D-flip-flop/latch with enable, allows for efficient use of the FPGA fabric. The VersaTile capability is unique to the ProASIC family of third-generation-architecture flash FPGAs. VersaTiles are connected with any of the four levels of routing hierarchy. Flash switches are distributed throughout the device to provide nonvolatile, reconfigurable interconnect programming. Maximum core utilization is possible for virtually any design.

Table 2-15 • Summary of I/O Input Buffer Power (per pin) – Default I/O Software Settings
Applicable to Advanced I/O Banks for A3P250 and A3P1000 Only

	VMV (V)	Static Power PDC6 (mW) ¹	Dynamic Power PAC9 (μW/MHz) ²
Single-Ended			
3.3 V LVTTTL / 3.3 V LVCMOS	3.3	–	16.22
3.3 V LVCMOS – Wide Range	3.3	–	16.22
2.5 V LVCMOS	2.5	–	4.65
1.8 V LVCMOS	1.8	–	1.65
1.5 V LVCMOS (JESD8-11)	1.5	–	0.98
3.3 V PCI	3.3	–	17.64
3.3 V PCI-X	3.3	–	17.64
Differential			
LVDS	2.5	2.26	0.83
LVPECL	3.3	5.72	1.81

Notes:

1. PDC6 is the static power (where applicable) measured on VMV.
2. PAC9 is the total dynamic power measured on VMV.

Table 2-16 • Summary of I/O Input Buffer Power (per pin) – Default I/O Software Settings
Applicable to Standard Plus I/O Banks for A3P250 and A3P1000 Only

	VMV (V)	Static Power PDC6 (mW) ¹	Dynamic Power PAC9 (μW/MHz) ²
Single-Ended			
3.3 V LVTTTL / 3.3 V LVCMOS	3.3	–	16.23
3.3 V LVCMOS – Wide Range	3.3	–	16.23
2.5 V LVCMOS	2.5	–	4.66
1.8 V LVCMOS	1.8	–	1.64
1.5 V LVCMOS (JESD8-11)	1.5	–	0.99
3.3 V PCI	3.3	–	17.64
3.3 V PCI-X	3.3	–	17.64

Notes:

1. PDC6 is the static power (where applicable) measured on VMV.
2. PAC9 is the total dynamic power measured on VMV.

Table 2-42 • I/O Short Currents I_{OSH}/I_{OSL}
Applicable to Standard Plus I/O Banks for A3P250 and A3P1000 Only

	Drive Strength	I _{OSL} (mA)*	I _{OSH} (mA)*
3.3 V LVTTTL / 3.3V LVCMOS	2mA	25	27
	4mA	25	27
	6mA	51	54
	8mA	51	54
	12mA	103	109
	16mA	103	109
3.3 V LVCMOS Wide Range	100 μ A	Same specification as regular LVCMOS 3.3 V	
2.5 V LVCMOS	2mA	16	18
	4mA	16	18
	6mA	32	37
	8mA	32	37
	12mA	65	74
1.8 V LVCMOS	2mA	9	11
	4mA	17	22
	6mA	35	44
	8mA	35	44
1.5V LVCMOS	2mA	13	16
	4mA	25	33
3.3 V PCI/PCI-X	Per PCI/PCI-X specification	103	109

Note: *T_J = 100°C

Table 2-43 • Schmitt Trigger Input Hysteresis, Hysteresis Voltage Value (typical) for Schmitt Mode Input Buffers Applicable to A3PE600L and A3PE3000L Only

Input Buffer Configuration	Hysteresis Value (typical)
3.3 V LVTTTL/LVCMOS/PCI/PCI-X (Schmitt trigger mode)	240 mV
2.5 V LVCMOS (Schmitt trigger mode)	140 mV
1.8 V LVCMOS (Schmitt trigger mode)	80 mV
1.5 V LVCMOS (Schmitt trigger mode)	60 mV
1.2 V LVCMOS (Schmitt trigger mode)	40 mV

The length of time an I/O can withstand I_{OSH}/I_{OSL} events depends on the junction temperature. The reliability data below is based on a 3.3 V, 12 mA I/O setting, which is the worst case for this type of analysis.

1.5 V DC Core Voltage

Table 2-88 • 1.8 V LVCMOS Low Slew

Military-Case Conditions: $T_J = 125^{\circ}\text{C}$, $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 1.7\text{ V}$

Applicable to Pro I/Os for A3PE600L and A3PE3000L Only

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.61	9.02	0.04	1.69	2.52	0.40	9.17	7.57	2.61	1.01	10.63	9.04	ns
	–1	0.52	7.68	0.03	1.44	2.14	0.34	7.80	6.44	2.22	0.86	9.04	7.69	ns
4 mA	Std.	0.61	7.41	0.04	1.69	2.52	0.40	7.52	6.36	3.07	2.56	8.99	7.83	ns
	–1	0.52	6.30	0.03	1.44	2.14	0.34	6.40	5.41	2.62	2.18	7.64	6.66	ns
6 mA	Std.	0.61	6.26	0.04	1.69	2.52	0.40	6.35	5.53	3.38	3.14	7.82	7.00	ns
	–1	0.52	5.33	0.03	1.44	2.14	0.34	5.40	4.71	2.88	2.67	6.65	5.95	ns
8 mA	Std.	0.61	5.88	0.04	1.69	2.52	0.40	5.96	5.37	3.45	3.30	7.42	6.83	ns
	–1	0.52	5.00	0.03	1.44	2.14	0.34	5.07	4.57	2.94	2.81	6.32	5.81	ns
12 mA	Std.	0.61	5.76	0.04	1.69	2.52	0.40	5.85	5.38	3.55	3.88	7.31	6.84	ns
	–1	0.52	4.90	0.03	1.44	2.14	0.34	4.97	4.57	3.02	3.30	6.22	5.82	ns
16 mA	Std.	0.61	5.76	0.04	1.69	2.52	0.40	5.85	5.38	3.55	3.88	7.31	6.84	ns
	–1	0.52	4.90	0.03	1.44	2.14	0.34	4.97	4.57	3.02	3.30	6.22	5.82	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-89 • 1.8 V LVCMOS High Slew

Military-Case Conditions: $T_J = 125^{\circ}\text{C}$, $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 1.7\text{ V}$

Applicable to Pro I/Os for A3PE600L and A3PE3000L Only

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.61	4.01	0.04	1.69	2.52	0.40	4.06	3.94	2.60	1.03	5.52	5.40	ns
	–1	0.52	3.41	0.03	1.44	2.14	0.34	3.45	3.35	2.21	0.88	4.70	4.60	ns
4 mA	Std.	0.61	3.22	0.04	1.69	2.52	0.40	3.26	2.89	3.07	2.65	4.72	4.36	ns
	–1	0.52	2.74	0.03	1.44	2.14	0.34	2.77	2.46	2.61	2.26	4.02	3.71	ns
6 mA	Std.	0.61	2.74	0.04	1.69	2.52	0.40	2.77	2.38	3.38	3.23	4.23	3.84	ns
	–1	0.52	2.33	0.03	1.44	2.14	0.34	2.36	2.02	2.88	2.75	3.60	3.27	ns
8 mA	Std.	0.61	2.65	0.04	1.69	2.52	0.40	2.68	2.28	3.45	3.40	4.14	3.75	ns
	–1	0.52	2.26	0.03	1.44	2.14	0.34	2.28	1.94	2.93	2.89	3.52	3.19	ns
12 mA	Std.	0.61	2.64	0.04	1.69	2.52	0.40	2.66	2.16	3.55	4.01	4.13	3.63	ns
	–1	0.52	2.24	0.03	1.44	2.14	0.34	2.26	1.84	3.02	3.41	3.51	3.08	ns
16 mA	Std.	0.61	2.64	0.04	1.69	2.52	0.40	2.66	2.16	3.55	4.01	4.13	3.63	ns
	–1	0.52	2.24	0.03	1.44	2.14	0.34	2.26	1.84	3.02	3.41	3.51	3.08	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

2.5 V GTL

Gunning Transceiver Logic is a high-speed bus standard (JESD8-3). It provides a differential amplifier input buffer and an open-drain output buffer. The V_{CCI} pin should be connected to 2.5 V.

Table 2-124 • Minimum and Maximum DC Input and Output Levels

2.5 V GTL	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
20 mA ⁵	-0.3	VREF - 0.05	VREF + 0.05	3.6	0.4	-	20	20	169	124	15	15

Notes:

- I_{IL} is the input leakage current per I/O pin over recommended operating conditions where $-0.3 \text{ V} < V_{IN} < V_{IL}$.
- I_{IH} is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges.
- Currents are measured at 100°C junction temperature and maximum voltage.
- Currents are measured at 125°C junction temperature.
- Output drive strength is below JEDEC specification.

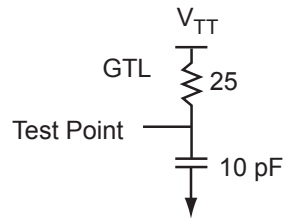


Figure 2-16 • AC Loading

Table 2-125 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	V_{TT} (typ.) (V)	C_{LOAD} (pF)
VREF - 0.05	VREF + 0.05	0.8	0.8	1.2	10

Note: *Measuring point = V_{trip} . See Table 2-29 on page 2-25 for a complete table of trip points.

Timing Characteristics

Table 2-126 • 2.5 V GTL

Military-Case Conditions: $T_J = 125^\circ\text{C}$, Worst-Case $V_{CC} = 1.14 \text{ V}$,
Worst-Case $V_{CCI} = 3.0 \text{ V}$, $V_{REF} = 0.8 \text{ V}$
Applicable to Pro I/Os for A3PE600L and A3PE3000L Only

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
Std.	0.80	2.11	0.05	2.26	0.52	2.14	2.11	-	-	4.34	4.31	ns
-1	0.68	1.79	0.05	1.93	0.44	1.82	1.79	-	-	3.70	3.68	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-127 • 2.5 V GTL

Military-Case Conditions: $T_J = 125^\circ\text{C}$, $V_{CC} = 1.425 \text{ V}$,
Worst-Case $V_{CCI} = 3.0 \text{ V}$, $V_{REF} = 0.8 \text{ V}$
Applicable to Pro I/Os for A3PE600L and A3PE3000L Only

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
Std.	0.61	2.02	0.04	2.04	0.40	1.98	2.02	-	-	3.45	3.49	ns
-1	0.52	1.72	0.03	1.73	0.34	1.69	1.72	-	-	2.93	2.97	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-139 • HSTL Class I
Military-Case Conditions: $T_J = 125^{\circ}\text{C}$, $V_{CC} = 1.425\text{ V}$,
Worst-Case $V_{CCI} = 1.4\text{ V}$, $V_{REF} = 0.75\text{ V}$
Applicable to Pro I/Os for A3PE600L and A3PE3000L Only

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
Std.	0.61	3.02	0.04	2.52	0.40	3.05	3.00	—	—	4.51	4.46	ns
–1	0.52	2.57	0.03	2.14	0.34	2.59	2.55	—	—	3.84	3.79	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Fully Registered I/O Buffers with Synchronous Enable and Asynchronous Clear

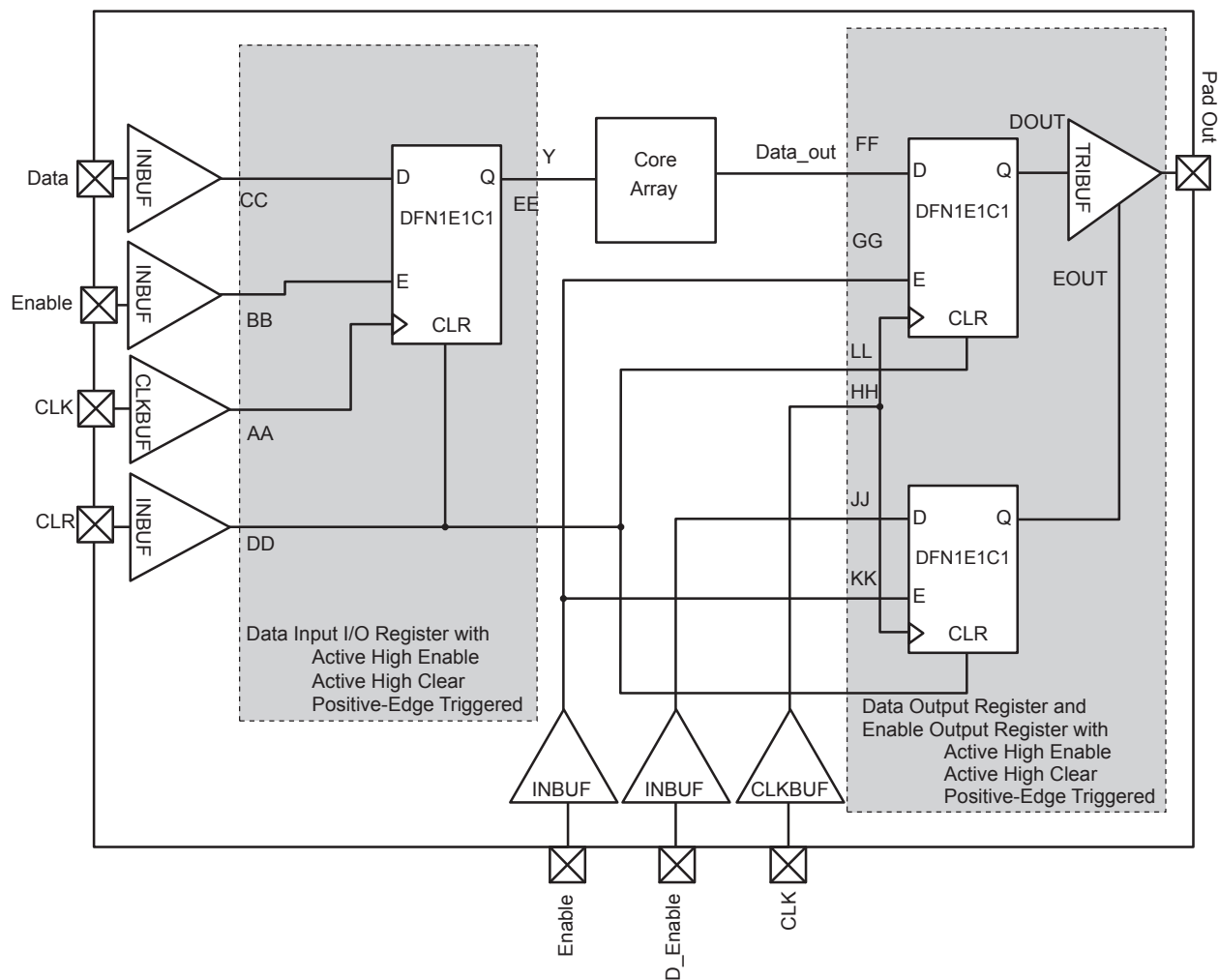


Figure 2-29 • Timing Model of the Registered I/O Buffers with Synchronous Enable and Asynchronous Clear

VersaTile Characteristics

VersaTile Specifications as a Combinatorial Module

The military ProASIC3 library offers all combinations of LUT-3 combinatorial functions. In this section, timing characteristics are presented for a sample of the library. For more details, refer to the [IGLOO](#), [Fusion](#), and [ProASIC3 Macro Library Guide](#).

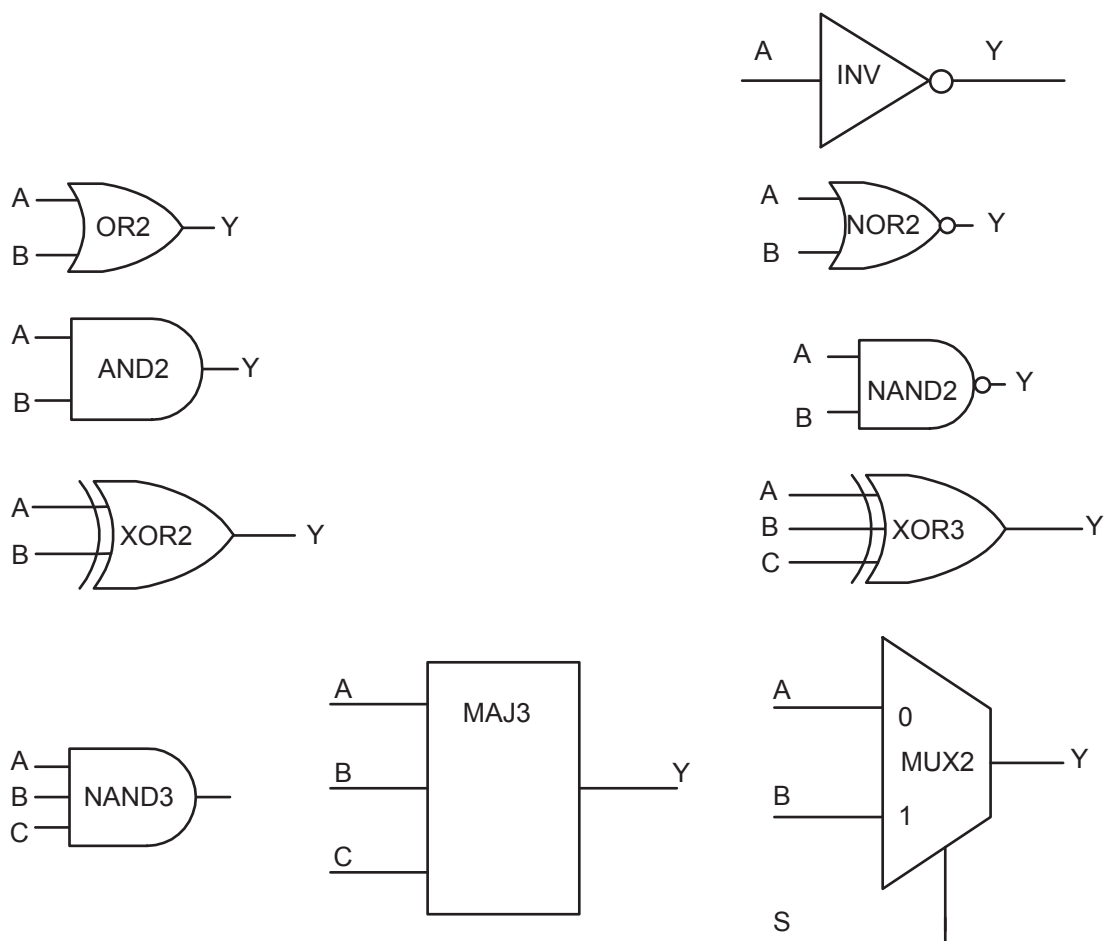


Figure 2-37 • Sample of Combinatorial Cells

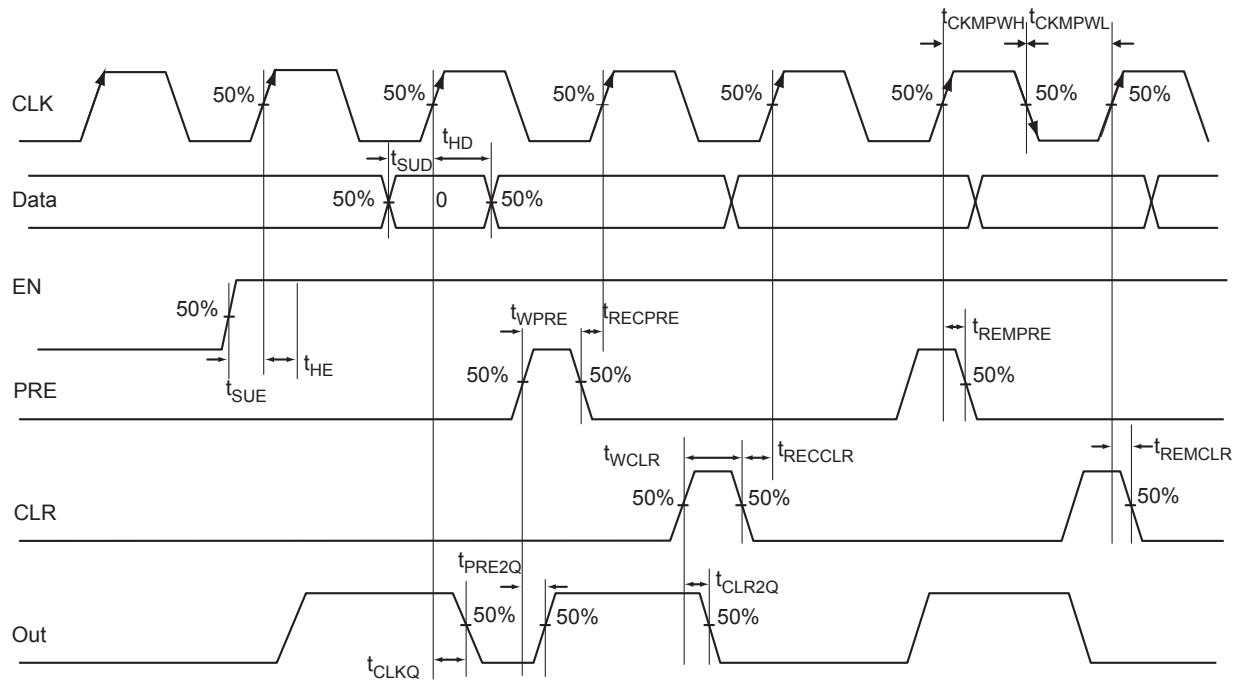


Figure 2-40 • Timing Model and Waveforms

1.5 V DC Core Voltage

Table 2-197 • A3PE600L Global Resource
Military-Case Conditions: $T_J = 125^{\circ}\text{C}$, $V_{CC} = 1.425\text{ V}$

Parameter	Description	–1		Std.		Units
		Min. ¹	Max. ²	Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	0.82	1.07	0.97	1.26	ns
t_{RCKH}	Input High Delay for Global Clock	0.81	1.10	0.95	1.30	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock					ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock					ns
t_{RCKSW}	Maximum Skew for Global Clock		0.30		0.35	ns
F_{RMAX}	Maximum Frequency for Global Clock					MHz

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-198 • A3PE3000L Global Resource
Military-Case Conditions: $T_J = 125^{\circ}\text{C}$, $V_{CC} = 1.425\text{ V}$

Parameter	Description	–1		Std.		Units
		Min. ¹	Max. ²	Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	1.62	1.87	1.90	2.20	ns
t_{RCKH}	Input High Delay for Global Clock	1.61	1.90	1.89	2.24	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock					ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock					ns
t_{RCKSW}	Maximum Skew for Global Clock		0.30		0.35	ns
F_{RMAX}	Maximum Frequency for Global Clock					MHz

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Embedded SRAM and FIFO Characteristics

SRAM

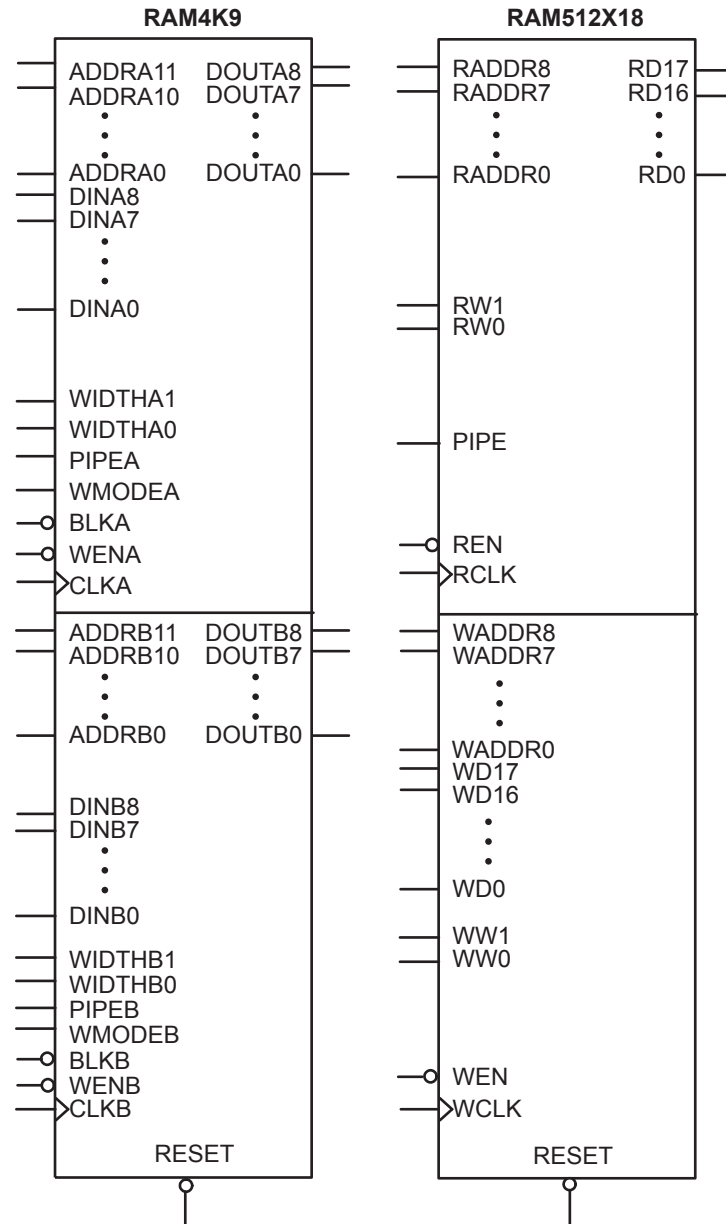


Figure 2-43 • RAM Models

Table 2-212 • FIFO Worst Military-Case Conditions: $T_J = 125^{\circ}\text{C}$, $V_{CC} = 1.425\text{ V}$ for A3P250 (256×16)

Parameter	Description	–1	Std.	Units
t_{ENS}	REN, WEN Setup Time	3.92	4.61	ns
t_{ENH}	REN, WEN Hold Time	0.00	0.00	ns
t_{BKS}	BLK Setup Time	1.66	1.95	ns
t_{BKH}	BLK Hold Time	0.00	0.00	ns
t_{DS}	Input Data (WD) Setup Time	0.22	0.26	ns
t_{DH}	Input Data (WD) Hold Time	0.00	0.00	ns
t_{CKQ1}	Clock HIGH to New Data Valid on RD (flow-through)	2.61	3.06	ns
t_{CKQ2}	Clock HIGH to New Data Valid on RD (pipelined)	1.14	1.34	ns
t_{RCKEF}	RCLK HIGH to Empty Flag Valid	2.07	2.43	ns
t_{WCKFF}	WCLK HIGH to Full Flag Valid	1.96	2.31	ns
t_{CKAF}	Clock HIGH to Almost Empty/Full Flag Valid	7.45	8.76	ns
t_{RSTFG}	RESET LOW to Empty/Full Flag Valid	2.04	2.40	ns
t_{RSTAF}	RESET LOW to Almost Empty/Full Flag Valid	7.38	8.67	ns
t_{RSTBQ}	RESET LOW to Data Out LOW on RD (flow-through)	1.11	1.31	ns
	RESET LOW to Data Out LOW on RD (pipelined)	1.11	1.31	ns
t_{REMRSTB}	RESET Removal	0.34	0.40	ns
t_{RECRSTB}	RESET Recovery	1.81	2.12	ns
t_{MPWRSTB}	RESET Minimum Pulse Width	0.26	0.30	ns
t_{CYC}	Clock Cycle Time	3.89	4.57	ns
F_{MAX}	Maximum Frequency for FIFO	257	219	MHz

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-7 on page 2-6](#) for derating values.

JTAG 1532 Characteristics

JTAG timing delays do not include JTAG I/Os. To obtain complete JTAG timing, add I/O buffer delays to the corresponding standard selected; refer to the I/O timing characteristics in the "User I/O Characteristics" section on page 2-18 for more details.

Timing Characteristics

Table 2-220 • JTAG 1532

Military-Case Conditions: $T_J = 125^\circ\text{C}$, Worst-Case $V_{CC} = 1.14\text{ V}$ for A3PE600L and A3PE3000L

Parameter	Description	–1	Std.	Units
t_{DISU}	Test Data Input Setup Time	0.80	0.94	ns
t_{DIHD}	Test Data Input Hold Time	1.60	1.88	ns
t_{TMSU}	Test Mode Select Setup Time	0.80	0.94	ns
t_{TMDHD}	Test Mode Select Hold Time	1.60	1.88	ns
t_{TCK2Q}	Clock to Q (data out)	6.39	7.52	ns
t_{RSTB2Q}	Reset to Q (data out)	26.63	31.33	ns
F_{TCKMAX}	TCK Maximum Frequency	18.70	15.90	MHz
t_{TRSTREM}	ResetB Removal Time	0.48	0.56	ns
t_{TRSTREC}	ResetB Recovery Time	0.00	0.00	ns
t_{TRSTMPW}	ResetB Minimum Pulse	TBD	TBD	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-221 • JTAG 1532

Military-Case Conditions: $T_J = 125^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$ for All Dies

Parameter	Description	–1	Std.	Units
t_{DISU}	Test Data Input Setup Time	0.60	0.71	ns
t_{DIHD}	Test Data Input Hold Time	1.21	1.42	ns
t_{TMSU}	Test Mode Select Setup Time	0.60	0.71	ns
t_{TMDHD}	Test Mode Select Hold Time	1.21	1.42	ns
t_{TCK2Q}	Clock to Q (data out)	6.04	7.10	ns
t_{RSTB2Q}	Reset to Q (data out)	24.15	28.41	ns
F_{TCKMAX}	TCK Maximum Frequency	22.00	19.00	MHz
t_{TRSTREM}	ResetB Removal Time	0.00	0.00	ns
t_{TRSTREC}	ResetB Recovery Time	0.24	0.28	ns
t_{TRSTMPW}	ResetB Minimum Pulse	TBD	TBD	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

VQ100	
Pin Number	A3P250 Function
1	GND
2	GAA2/IO118UDB3
3	IO118VDB3
4	GAB2/IO117UDB3
5	IO117VDB3
6	GAC2/IO116UDB3
7	IO116VDB3
8	IO112PSB3
9	GND
10	GFB1/IO109PDB3
11	GFB0/IO109NDB3
12	VCOMPLF
13	GFA0/IO108NPB3
14	VCCPLF
15	GFA1/IO108PPB3
16	GFA2/IO107PSB3
17	VCC
18	VCCIB3
19	GFC2/IO105PSB3
20	GEC1/IO100PDB3
21	GEC0/IO100NDB3
22	GEA1/IO98PDB3
23	GEA0/IO98NDB3
24	VMV3
25	GNDQ
26	GEA2/IO97RSB2
27	GEB2/IO96RSB2
28	GEC2/IO95RSB2
29	IO93RSB2
30	IO92RSB2
31	IO91RSB2
32	IO90RSB2
33	IO88RSB2
34	IO86RSB2
35	IO85RSB2
36	IO84RSB2

VQ100	
Pin Number	A3P250 Function
37	VCC
38	GND
39	VCCIB2
40	IO77RSB2
41	IO74RSB2
42	IO71RSB2
43	GDC2/IO63RSB2
44	GDB2/IO62RSB2
45	GDA2/IO61RSB2
46	GNDQ
47	TCK
48	TDI
49	TMS
50	VMV2
51	GND
52	VPUMP
53	NC
54	TDO
55	TRST
56	VJTAG
57	GDA1/IO60USB1
58	GDC0/IO58VDB1
59	GDC1/IO58UDB1
60	IO52NDB1
61	GCB2/IO52PDB1
62	GCA1/IO50PDB1
63	GCA0/IO50NDB1
64	GCC0/IO48NDB1
65	GCC1/IO48PDB1
66	VCCIB1
67	GND
68	VCC
69	IO43NDB1
70	GBC2/IO43PDB1
71	GBB2/IO42PSB1
72	IO41NDB1

VQ100	
Pin Number	A3P250 Function
73	GBA2/IO41PDB1
74	VMV1
75	GNDQ
76	GBA1/IO40RSB0
77	GBA0/IO39RSB0
78	GBB1/IO38RSB0
79	GBB0/IO37RSB0
80	GBC1/IO36RSB0
81	GBC0/IO35RSB0
82	IO29RSB0
83	IO27RSB0
84	IO25RSB0
85	IO23RSB0
86	IO21RSB0
87	VCCIB0
88	GND
89	VCC
90	IO15RSB0
91	IO13RSB0
92	IO11RSB0
93	GAC1/IO05RSB0
94	GAC0/IO04RSB0
95	GAB1/IO03RSB0
96	GAB0/IO02RSB0
97	GAA1/IO01RSB0
98	GAA0/IO00RSB0
99	GNDQ
100	VMV0

FG256	
Pin Number	A3P1000 Function
R5	IO168RSB2
R6	IO163RSB2
R7	IO157RSB2
R8	IO149RSB2
R9	IO143RSB2
R10	IO138RSB2
R11	IO131RSB2
R12	IO125RSB2
R13	GDB2/IO115RSB2
R14	TDI
R15	GNDQ
R16	TDO
T1	GND
T2	IO183RSB2
T3	GEB2/IO186RSB2
T4	IO172RSB2
T5	IO170RSB2
T6	IO164RSB2
T7	IO158RSB2
T8	IO153RSB2
T9	IO142RSB2
T10	IO135RSB2
T11	IO130RSB2
T12	GDC2/IO116RSB2
T13	IO120RSB2
T14	GDA2/IO114RSB2
T15	TMS
T16	GND

FG484		FG484		FG484	
Pin Number	A3PE600L Function	Pin Number	A3PE600L Function	Pin Number	A3PE600L Function
R8	VMV5	T21	IO64PDB3V1	V12	IO83PDB5V0
R9	VCCIB5	T22	IO62NDB3V1	V13	IO77NDB4V1
R10	VCCIB5	U1	NC	V14	IO77PDB4V1
R11	IO84NDB5V0	U2	IO107PDB6V0	V15	IO69NDB4V0
R12	IO84PDB5V0	U3	IO107NDB6V0	V16	GDB2/IO69PDB4V0
R13	VCCIB4	U4	GEB1/IO103PDB6V0	V17	TDI
R14	VCCIB4	U5	GEB0/IO103NDB6V0	V18	GNDQ
R15	VMV3	U6	VMV6	V19	TDO
R16	VCCPLD	U7	VCCPLE	V20	GND
R17	GDB1/IO66PPB3V1	U8	IO101NPB5V2	V21	NC
R18	GDC1/IO65PDB3V1	U9	IO95PPB5V1	V22	IO63NDB3V1
R19	IO61NDB3V1	U10	IO92PDB5V1	W1	NC
R20	VCC	U11	IO90PDB5V1	W2	NC
R21	IO59NDB3V0	U12	IO82PDB5V0	W3	NC
R22	IO62PDB3V1	U13	IO76NDB4V1	W4	GND
T1	NC	U14	IO76PDB4V1	W5	IO100NDB5V2
T2	IO110NDB6V0	U15	VMV4	W6	FF/GEB2/IO100PDB5V2
T3	NC	U16	TCK	W7	IO99NDB5V2
T4	IO105PDB6V0	U17	VPUMP	W8	IO88NDB5V0
T5	IO105NDB6V0	U18	TRST	W9	IO88PDB5V0
T6	GEC1/IO104PPB6V0	U19	GDA0/IO67NDB3V1	W10	IO89NDB5V0
T7	VCOMPLE	U20	NC	W11	IO80NDB4V1
T8	GNDQ	U21	IO64NDB3V1	W12	IO81NDB4V1
T9	GEA2/IO101PPB5V2	U22	IO63PDB3V1	W13	IO81PDB4V1
T10	IO92NDB5V1	V1	NC	W14	IO70NDB4V0
T11	IO90NDB5V1	V2	NC	W15	GDC2/IO70PDB4V0
T12	IO82NDB5V0	V3	GND	W16	IO68NDB4V0
T13	IO74NDB4V1	V4	GEA1/IO102PDB6V0	W17	GDA2/IO68PDB4V0
T14	IO74PDB4V1	V5	GEA0/IO102NDB6V0	W18	TMS
T15	GNDQ	V6	GNDQ	W19	GND
T16	VCOMPLD	V7	GEC2/IO99PDB5V2	W20	NC
T17	VJTAG	V8	IO95NPB5V1	W21	NC
T18	GDC0/IO65NDB3V1	V9	IO91NDB5V1	W22	NC
T19	GDA1/IO67PDB3V1	V10	IO91PDB5V1	Y1	VCCIB6
T20	NC	V11	IO83NDB5V0	Y2	NC

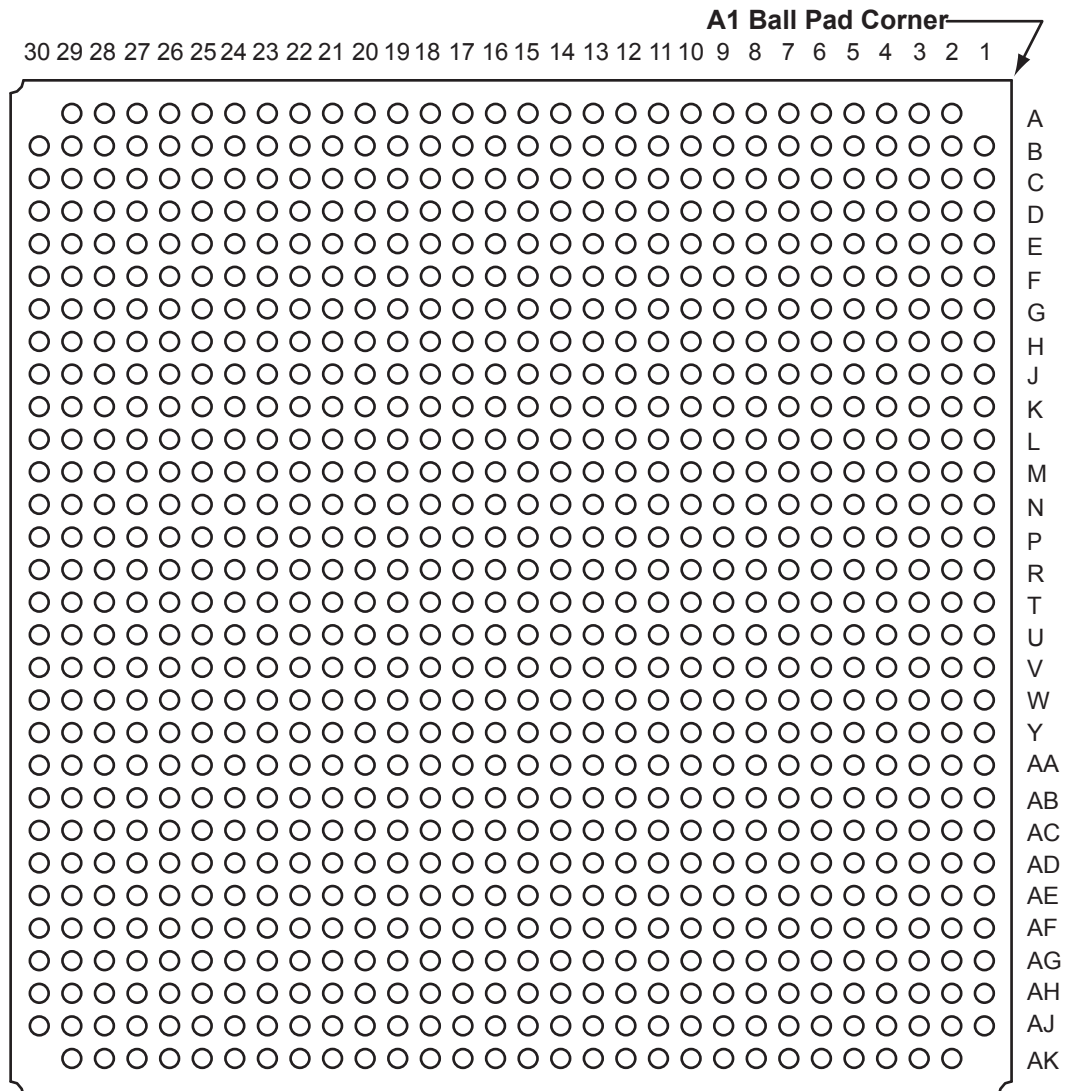
FG484	
Pin Number	A3PE600L Function
Y3	NC
Y4	IO98NDB5V2
Y5	GND
Y6	IO94NDB5V1
Y7	IO94PDB5V1
Y8	VCC
Y9	VCC
Y10	IO89PDB5V0
Y11	IO80PDB4V1
Y12	IO78NPB4V1
Y13	NC
Y14	VCC
Y15	VCC
Y16	NC
Y17	NC
Y18	GND
Y19	NC
Y20	NC
Y21	NC
Y22	VCCIB3
AA1	GND
AA2	VCCIB6
AA3	NC
AA4	IO98PDB5V2
AA5	IO96NDB5V2
AA6	IO96PDB5V2
AA7	IO86NDB5V0
AA8	IO86PDB5V0
AA9	IO85PDB5V0
AA10	IO85NDB5V0
AA11	IO78PPB4V1
AA12	IO79NDB4V1
AA13	IO79PDB4V1
AA14	NC
AA15	NC

FG484	
Pin Number	A3PE600L Function
AA16	IO71NDB4V0
AA17	IO71PDB4V0
AA18	NC
AA19	NC
AA20	NC
AA21	VCCIB3
AA22	GND
AB1	GND
AB2	GND
AB3	VCCIB5
AB4	IO97NDB5V2
AB5	IO97PDB5V2
AB6	IO93NDB5V1
AB7	IO93PDB5V1
AB8	IO87NDB5V0
AB9	IO87PDB5V0
AB10	NC
AB11	NC
AB12	IO75NDB4V1
AB13	IO75PDB4V1
AB14	IO72NDB4V0
AB15	IO72PDB4V0
AB16	IO73NDB4V0
AB17	IO73PDB4V0
AB18	NC
AB19	NC
AB20	VCCIB4
AB21	GND
AB22	GND

FG484		FG484		FG484	
Pin Number	A3P1000 Function	Pin Number	A3P1000 Function	Pin Number	A3P1000 Function
E18	GBA2/IO78PDB1	G9	IO23RSB0	H22	NC
E19	IO81PDB1	G10	IO29RSB0	J1	IO212NDB3
E20	GND	G11	IO33RSB0	J2	IO212PDB3
E21	NC	G12	IO46RSB0	J3	NC
E22	IO84PDB1	G13	IO52RSB0	J4	IO217NDB3
F1	NC	G14	IO60RSB0	J5	IO218NDB3
F2	IO215PDB3	G15	GNDQ	J6	IO216PDB3
F3	IO215NDB3	G16	IO80NDB1	J7	IO216NDB3
F4	IO224NDB3	G17	GBB2/IO79PDB1	J8	VCCIB3
F5	IO225NDB3	G18	IO79NDB1	J9	GND
F6	VMV3	G19	IO82NPB1	J10	VCC
F7	IO11RSB0	G20	IO85PDB1	J11	VCC
F8	GAC0/IO04RSB0	G21	IO85NDB1	J12	VCC
F9	GAC1/IO05RSB0	G22	NC	J13	VCC
F10	IO25RSB0	H1	NC	J14	GND
F11	IO36RSB0	H2	NC	J15	VCCIB1
F12	IO42RSB0	H3	VCC	J16	IO83NPB1
F13	IO49RSB0	H4	IO217PDB3	J17	IO86NPB1
F14	IO56RSB0	H5	IO218PDB3	J18	IO90PPB1
F15	GBC0/IO72RSB0	H6	IO221NDB3	J19	IO87NDB1
F16	IO62RSB0	H7	IO221PDB3	J20	NC
F17	VMV0	H8	VMV0	J21	IO89PDB1
F18	IO78NDB1	H9	VCCIB0	J22	IO89NDB1
F19	IO81NDB1	H10	VCCIB0	K1	IO211PDB3
F20	IO82PPB1	H11	IO38RSB0	K2	IO211NDB3
F21	NC	H12	IO47RSB0	K3	NC
F22	IO84NDB1	H13	VCCIB0	K4	IO210PPB3
G1	IO214NDB3	H14	VCCIB0	K5	IO213NDB3
G2	IO214PDB3	H15	VMV1	K6	IO213PDB3
G3	NC	H16	GBC2/IO80PDB1	K7	GFC1/IO209PPB3
G4	IO222NDB3	H17	IO83PPB1	K8	VCCIB3
G5	IO222PDB3	H18	IO86PPB1	K9	VCC
G6	GAC2/IO223PDB3	H19	IO87PDB1	K10	GND
G7	IO223NDB3	H20	VCC	K11	GND
G8	GNDQ	H21	NC	K12	GND

FG484		FG484		FG484	
Pin Number	A3P1000 Function	Pin Number	A3P1000 Function	Pin Number	A3P1000 Function
K13	GND	M4	GFA2/IO206PDB3	N17	IO100NPB1
K14	VCC	M5	GFA1/IO207PDB3	N18	IO102NDB1
K15	VCCIB1	M6	VCCPLF	N19	IO102PDB1
K16	GCC1/IO91PPB1	M7	IO205NDB3	N20	NC
K17	IO90NPB1	M8	GFB2/IO205PDB3	N21	IO101NPB1
K18	IO88PDB1	M9	VCC	N22	IO103PDB1
K19	IO88NDB1	M10	GND	P1	NC
K20	IO94NPB1	M11	GND	P2	IO199PDB3
K21	IO98NDB1	M12	GND	P3	IO199NDB3
K22	IO98PDB1	M13	GND	P4	IO202NDB3
L1	NC	M14	VCC	P5	IO202PDB3
L2	IO200PDB3	M15	GCB2/IO95PPB1	P6	IO196PPB3
L3	IO210NPB3	M16	GCA1/IO93PPB1	P7	IO193PPB3
L4	GFB0/IO208NPB3	M17	GCC2/IO96PPB1	P8	VCCIB3
L5	GFA0/IO207NDB3	M18	IO100PPB1	P9	GND
L6	GFB1/IO208PPB3	M19	GCA2/IO94PPB1	P10	VCC
L7	VCOMPLF	M20	IO101PPB1	P11	VCC
L8	GFC0/IO209NPB3	M21	IO99PPB1	P12	VCC
L9	VCC	M22	NC	P13	VCC
L10	GND	N1	IO201NDB3	P14	GND
L11	GND	N2	IO201PDB3	P15	VCCIB1
L12	GND	N3	NC	P16	GDB0/IO112NPB1
L13	GND	N4	GFC2/IO204PDB3	P17	IO106NDB1
L14	VCC	N5	IO204NDB3	P18	IO106PDB1
L15	GCC0/IO91NPB1	N6	IO203NDB3	P19	IO107PDB1
L16	GCB1/IO92PPB1	N7	IO203PDB3	P20	NC
L17	GCA0/IO93NPB1	N8	VCCIB3	P21	IO104PDB1
L18	IO96NPB1	N9	VCC	P22	IO103NDB1
L19	GCB0/IO92NPB1	N10	GND	R1	NC
L20	IO97PDB1	N11	GND	R2	IO197PPB3
L21	IO97NDB1	N12	GND	R3	VCC
L22	IO99NPB1	N13	GND	R4	IO197NPB3
M1	NC	N14	VCC	R5	IO196NPB3
M2	IO200NDB3	N15	VCCIB1	R6	IO193NPB3
M3	IO206NDB3	N16	IO95NPB1	R7	GEC0/IO190NPB3

FG896



Note: This is the bottom view.

Note

For Package Manufacturing and Environmental information, visit the Resource Center at <http://www.microsemi.com/products/fpga-soc/solutions>.